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November 2010

### **FDMC6296**

# Single N-Channel Logic-Level Power Trench® MOSFET 30 V, 11.5 A, 10.5 m $\Omega$

#### **Features**

- Max  $r_{DS(on)}$  = 10.5 m $\Omega$  at  $V_{GS}$  = 10 V,  $I_D$  = 11.5 A
- Max  $r_{DS(on)}$  = 15 m $\Omega$  at  $V_{GS}$  = 4.5 V,  $I_D$  = 10 A
- Low Qg, Qgd and Rg for efficient switching performance
- RoHS Compliant

#### **General Description**

This single N-Channel MOSFET in the thermally efficient MicroFET Package has been specifically designed to perform well in Point of Load converters. Providing an optimized balance between  $r_{\text{DS(on)}}$  and gate charge this device can be effectively used as a "high side" control swtich or "low side" synchronous rectifier.

#### **Application**



- Point of Load Converters
- 1/16 Brick Synchronous Rectifier

### 

#### MOSFET Maximum Ratings T<sub>A</sub> = 25 °C unless otherwise noted

Symbol	Parameter				Ratings	Units
$V_{DS}$	Drain to Source Vo	Itage			30	V
$V_{GS}$	Gate to Source Vol	tage			±20	V
1	Drain Current	-Continuous	T <sub>A</sub> = 25 °C	(Note 1a)	11.5	Α
ID		-Pulsed			40	
D	Power Dissipation		T <sub>C</sub> = 25 °C		2.1	W
$P_{D}$	Power Dissipation		T <sub>A</sub> = 25 °C	(Note 1a)	0.9	VV
T <sub>J</sub> , T <sub>STG</sub>	Operating and Stor	age Junction Temperatu	ire Range		-55 to +150	°C

#### **Thermal Characteristics**

$R_{\theta JC}$	Thermal Resistance, Junction to Case	(Note 1)	3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	53	C/VV

#### **Package Marking and Ordering Information**

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC6296	FDMC6296	MLP 3.3X3.3	13 "	12 mm	3000 units

### **Electrical Characteristics** $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Chara	acteristics					
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, referenced to 25 °C		26		mV/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24 V, V <sub>GS</sub> = 0 V			1	μΑ
I <sub>GSS</sub>	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA

#### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \mu A$	1	1.8	3	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \mu A$ , referenced to 25 °C		-6		mV/°C
		$V_{GS} = 10 \text{ V}, I_D = 11.5 \text{ A}$		8.7	10.5	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$		10.6	15	mΩ
		$V_{GS} = 10 \text{ V}, I_D = 11.5 \text{ A}, T_J = 125 ^{\circ}\text{C}$		13	17	
9 <sub>FS</sub>	Forward Transconductance	V <sub>DD</sub> = 5 V, I <sub>D</sub> = 11.5 A		49		S

### **Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V 45.V.V 0.V	1610	2141	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$ $f = 1 \text{ MHz}$	406	540	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1 1011 12	150	225	pF
$R_{g}$	Gate Resistance	V <sub>GS</sub> = 0 V, f = 1 MHz	0.9		Ω

#### **Switching Characteristics**

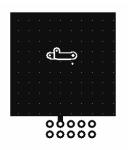
t <sub>d(on)</sub>	Turn-On Delay Time		10	20	ns
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 1.0 A,	3	10	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	$V_{GS} = 10 \text{ V}, R_{GEN} = 6 \Omega$	27	43	ns
t <sub>f</sub>	Fall Time		8	16	ns
$Q_{g(TOT)}$	Total Gate Charge at 5V	V <sub>GS</sub> = 5 V	14	19	nC
Q <sub>gs</sub>	Total Gate Charge	V <sub>DD</sub> = 15 V,	4		nC
$Q_{gd}$	Gate to Drain "Miller" Charge	I <sub>D</sub> = 11.5 A	4		nC

#### **Drain-Source Diode Characteristics**

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0 \text{ V}, I_S = 2 \text{ A}$ (Note 2)		0.7	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 11.5 A, di/dt = 100 A/μs 30 22			ns	
Q <sub>rr</sub>	Reverse Recovery Charge				nC	

#### Notes:

<sup>1.</sup> R<sub>0,1A</sub> is determined with the device mounted on a 1in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>0,1C</sub> is guaranteed by design while R<sub>0,1C</sub> is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300  $\mu$ s, Duty cycle < 2.0%.

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

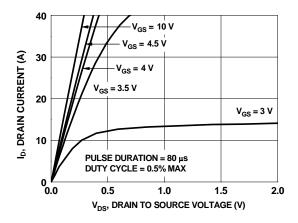


Figure 1. On Region Characteristics

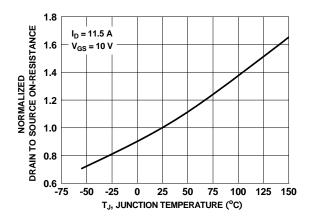


Figure 3. Normalized On Resistance vs Junction Temperature

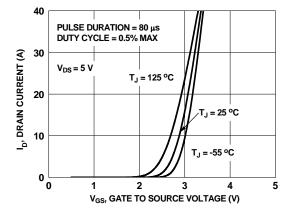


Figure 5. Transfer Characteristics

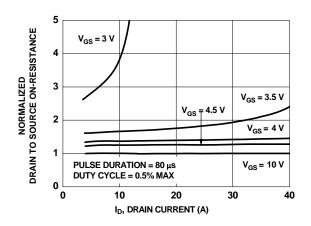


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

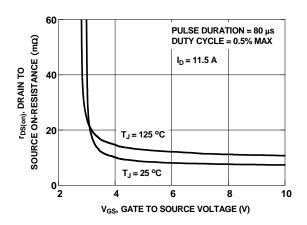


Figure 4. On-Resistance vs Gate to Source Voltage

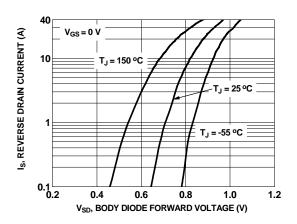


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

### Typical Characteristics T<sub>J</sub> = 25°C unless otherwise noted

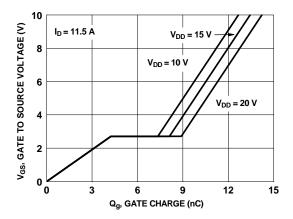


Figure 7. Gate Charge Characteristics

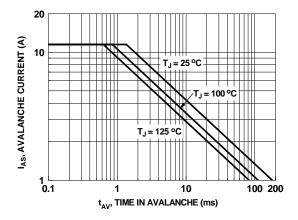


Figure 9. Unclamped Inductive Switching Capability

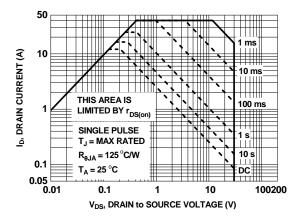


Figure 11. Forward Bias Safe Operating Area

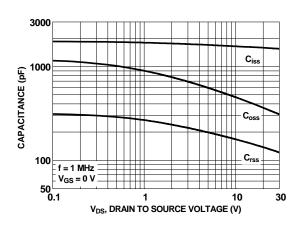


Figure 8. Capacitance vs Drain to Source Voltage

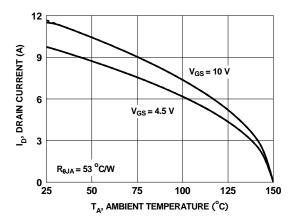


Figure 10. Maximum Continuous Drain Current vs Ambient Temperature

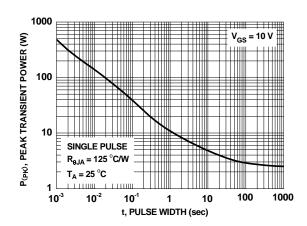


Figure 12. Single Pulse Maximum Power Dissipation

### **Typical Characteristics** $T_J = 25$ °C unless otherwise noted

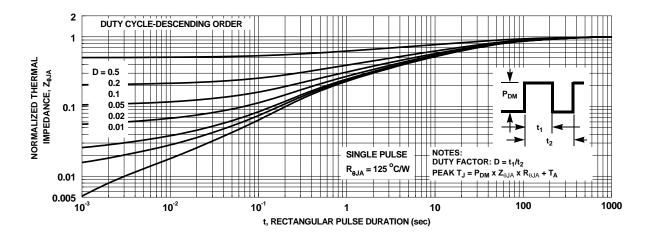
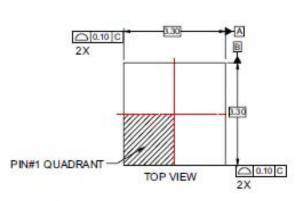
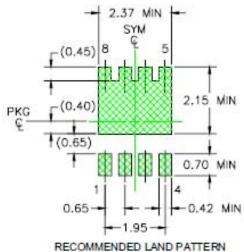
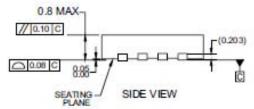


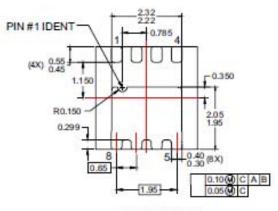
Figure 13. Junction-to-Ambient Transient Thermal Response Curve

### **Dimensional Outline and Pad Layout**









BOTTOM VIEW

#### NOTES:

- A. DOES NOT CONFORM TO JEDEC REGISTRATION MO-229
- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994
- D. DRAWING FILE NAME: MLP08SREVA
- E. LAND PATTERN RECOMMENDATION IS BASED ON FSC DESIGN ONLY





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